- State-of-the-Art *EPIC-*II*B*[™] BiCMOS Design Significantly Reduces Power Dissipation
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C
- High-Drive Outputs (–32-mA I_{OH}, 64-mA I_{OL})
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Plastic (N) and Ceramic (J) DIPs, and Ceramic Flat (W) Package

description

These octal buffers and line drivers are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. Together with the SN54ABT240, SN74ABT240A, and 'ABT244A, these devices provide the choice of selected combinations of inverting and noninverting outputs, symmetrical active-low output-enable (\overline{OE}) inputs, and complementary OE and \overline{OE} inputs.

SN54ABT241 J OR W PACKAGE
SN74ABT241A DB, DW, N, OR PW PACKAGE
(TOP VIEW)

SN54ABT241 . . . FK PACKAGE (TOP VIEW)

	2Y4 1A1 1 <u>A</u> E	Vcc 20E	
1A2 2Y3	321 4	20 19 18	[1Y1
2Y3	5	17	2A4
1A3] 4 ³ 2 1] 5] 6	16	[1Y2
1A3 2Y2 1A4] 7	15	2A3
1A4	8	14	[1Y3
	9 10 1	1 12 13	
	2Y1 GND	4 4 A	
	v ∰ v	$5 \rightarrow 6$	

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN54ABT241 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT241A is characterized for operation from –40°C to 85°C.



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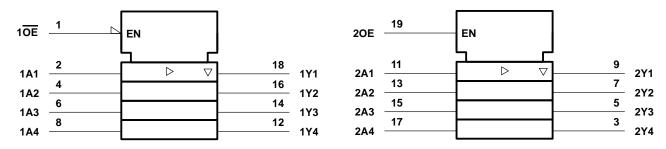
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FUNCTION TABLES

INPU	JTS	OUTPUT
10E	1A	1Y
L	Н	Н
L	L	L
Н	Х	Z

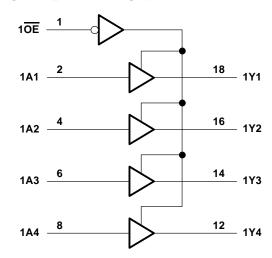
INP	JTS	OUTPUT
20E	2A	2Y
н	Н	Н
н	L	L
L	Х	Z

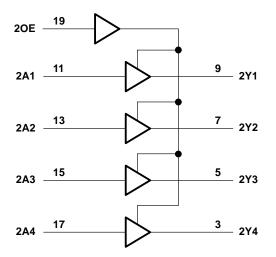
logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)







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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} Input voltage range, V _I (see Note 1)		
Voltage range applied to any output in the high	or power-off state, V _O	–0.5 V to 5.5 V
Current into any output in the low state, IO: SN	N54ABT241	
SN	N74ABT241A	128 mA
Input clamp current, I _{IK} (V _I < 0)		–18 mA
Output clamp current, I_{OK} (V _O < 0)		–50 mA
Package thermal impedance, θ_{JA} (see Note 2)	: DB package	115°C/W
	DW package	
	N package	67°C/W
	PW package	128°C/W
Storage temperature range, T _{stg}		–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions (see Note 3)

					SN74AB	T241A	UNIT
			MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage		4.5	5.5	4.5	5.5	V
VIH	VIH High-level input voltage		2		2		V
VIL	VIL Low-level input voltage			0.8		0.8	V
VI Input voltage			0	VCC	0	VCC	V
ЮН	High-level output current			-24		-32	mA
IOL	IOL Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	n rise or fall rate Outputs enabled		5		5	ns/V
Т _А	T _A Operating free-air temperature		-55	125	-40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

		TEST CONDITIONS		Т	A = 25°C	;	SN54A	BT241	SN74ABT241A		
PARA	METER	TEST COND	TIONS	MIN	TYP†	MAX	MIN	MAX	MIN	MAX	UNIT
VIK		V _{CC} = 4.5 V,	lj = –18 mA			-1.2		-1.2		-1.2	V
		V _{CC} = 4.5 V,	I _{OH} = -3 mA	2.5			2.5		2.5		
Val		V _{CC} = 5 V,	I _{OH} = -3 mA	3			3		3		v
VOH	OH V _{CC} = 4.5 V		I _{OH} = -24 mA	2			2				v
		VCC = 4.5 V	I _{OH} = -32 mA	2*					2		
VOL		V _{CC} = 4.5 V	I _{OL} = 48 mA			0.55		0.55			v
VOL		VCC = 4.3 V	I _{OL} = 64 mA			0.55*				0.55	V
V _{hys}					100						mV
lj		V _{CC} = 5.5 V,	$V_I = V_{CC}$ or GND			±1		±1		±1	μA
IOZH		V _{CC} = 5.5 V,	V _O = 2.7 V			10		10		10	μA
IOZL		V _{CC} = 5.5 V,	V _O = 0.5 V			-10		-10		-10	μΑ
l _{off}		V _{CC} = 0,	$V_I \text{ or } V_O \leq 4.5 \text{ V}$			±100				±100	μA
ICEX		$V_{CC} = 5.5 \text{ V}, \text{ V}_{O} = 5.5 \text{ V}$	Outputs high			50		50		50	μA
10‡		V _{CC} = 5.5 V,	V _O = 2.5 V	-50	-100	-180	-50	-180	-50	-180	mA
			Outputs high		1	250		250		250	μA
ICC		$V_{CC} = 5.5 \text{ V}, I_O = 0,$ $V_I = V_{CC} \text{ or GND}$	Outputs low		24	30		30		30	mA
			Outputs disabled		0.5	250		250		250	μA
	Data	V _{CC} = 5.5 V, One input at 3.4 V,	Outputs enabled			1.5		1.5		1.5	
∆ICC§	s inputs C	inputs Other inputs at V _{CC} or GND	Outputs disabled			0.05		0.05		0.05	mA
	Control inputs	V_{CC} = 5.5 V, One input at Other inputs at V_{CC} or GN				1.5		1.5		1.5	
Ci		V _l = 2.5 V or 0.5 V			4						pF
Co		V _O = 2.5 V or 0.5 V			5.5						рF

* On products compliant to MIL-PRF-38535, this parameter does not apply.

[†] All typical values are at $V_{CC} = 5$ V.

[‡]Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.



switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

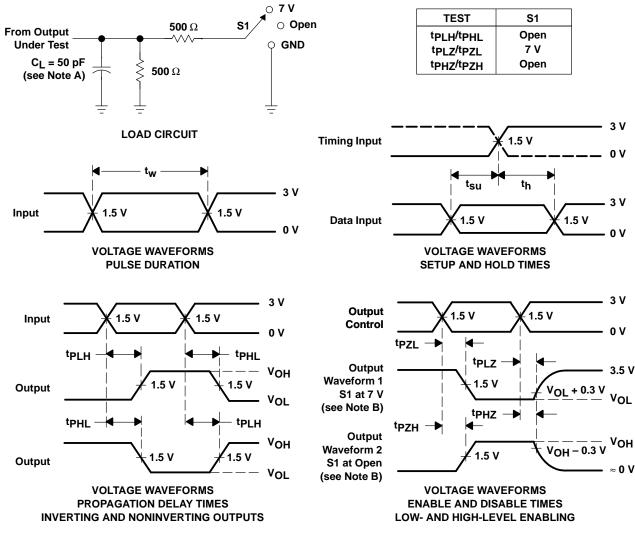
				SN	54ABT2	41		
PARAMETER	FROM (INPUT)			CC = 5 V A = 25°C	l, ;	MIN	МАХ	UNIT
			MIN	TYP	MAX			
^t PLH	A	V	1	2.6	4.1	0.8	5.3	ns
^t PHL		Ι	1	2.9	4.2	0.8	5	115
^t PZH	OE or OE	v	1.1	4.8	6.3	1	7	ns
^t PZL		Ι	1.3	4.3	5.8	1	7	115
^t PHZ	OE or OE	V	1.1	4.6	6.1	0.8	7.9	ns
^t PLZ	OE OF OE	1	1	3.9	5.4	0.8	6.2	115

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

				SN7	4ABT24	1 A		
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 5 V, T _A = 25°C			MIN	МАХ	UNIT
			MIN	TYP	MAX			
^t PLH	A	v	1	2.6	4.1	1	4.6	ns
^t PHL		I	1	2.9	4.4	1	4.6	115
^t PZH		V	1.1	4.8	6.3	1.1	6.8	ns
^t PZL	OE or OE	I	1.3	4.3	5.8	1.3	6.8	115
^t PHZ	OE or OE	v	1.6	4.6	6.1	1.6	7.1	ns
^t PLZ		1	1	3.9	5.4	1	5.9	115



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PARAMETER MEASUREMENT INFORMATION

NOTES: A. CL includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_f \leq 2.5 ns, t_f \leq 2.5 ns.

D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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